



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{SSS}	R _{SS(ON) Max}	I _{S Max} T _A = +25°C
401/	$2.75 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	20.2A
12V	6.1mΩ @ V _{GS} = 2.5V	13.6A

Features

- CSP with Footprint 2.98mm x 1.49mm
- Height = 0.11mm for Low Profile
- ESD Protection of Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{SS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Mechanical Data

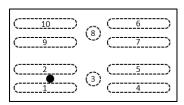
- Case: X4-DSN3015-10
- Terminal Connections: See Diagram Below
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu or NiAu. Solderable per MIL-STD-202, Method 208 @4

Applications

- Battery Management
- Load Switch
- Battery Protection

ESD PROTECTED



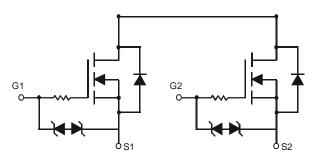


Source 1: 1,2,4,5

Gate 1: 3

Source 2: 6, 7, 9, 10

Gate 2: 8



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN12M7UCA10-7	X4-DSN3015-10	5000/Tape & Reel

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

Top View

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



 $\begin{array}{l} MF = Product\ Type\ Marking\ Code \\ YM = Date\ Code\ Marking \\ Y\ or\ \overline{Y} = Year\ (ex:\ F = 2018) \\ M\ or\ \overline{M} = Month\ (ex:\ 9 = September) \end{array}$

Date Code Key

Date Code Ite	<i>-</i>											
Year	2018	2019	20	020	2021	2022	2	2023	2024	20:	25	2026
Code	F	G		Н		J		K	L	N	1	N
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Source-Source Voltage	Vsss	12	V		
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Source Current (Note 5) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	Is	20.2 16.1	А
Continuous Source Current (Note 5) V _{GS} = 2.5V	Steady State	T _A = +25°C T _A = +70°C	Is	13.6 10.8	А
Pulsed Source Current (Note 6)	I _{SM}	80	Α		

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	P _D	0.74	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 7)	$R_{\theta JA}$	171.9	°C/W
Power Dissipation (Note 5)	P _D	1.73	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	$R_{\theta JA}$	74.4	°C/W
Operating and Storage Temperature Range	T_{J}, T_{STG}	-55 to +150	°C

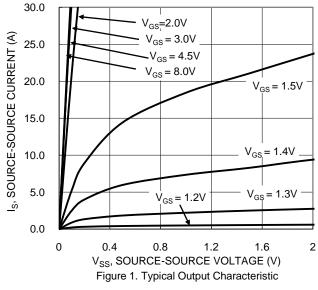
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	- Cymiaei		. , , ,	max	<u> </u>	root containen	
Source-Source Breakdown Voltage	BV _{SSS}	12	_	_	V	$V_{GS} = 0V$, $I_S = 1mA$	
Zero Gate Voltage Drain Current T _J = +25°C	Isss	_	_	1	μΑ	V _{SS} = 9.6V, V _{GS} = 0V	
Cata Cauraa Laakaga		_	_	±10	μΑ	$V_{GS} = \pm 8V$, $V_{SS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±1	μΑ	$V_{GS} = \pm 5V$, $V_{SS} = 0V$	
ON CHARACTERISTICS (Note 8)						•	
Gate Threshold Voltage	V _{GS(TH)}	0.5	0.8	1.4	V	Vss = 10V, Is = 1.11mA	
		1.55	2.19	2.75		$V_{GS} = 4.5V, I_{S} = 6A$	
Static Source Source On Desintence	_	1.6	2.30	2.85		$V_{GS} = 3.8V, I_S = 6A$	
Static Source-Source On-Resistance	R _{SS(ON)}	1.65	2.51	3.95	mΩ	V _{GS} = 3.1V, I _S = 6A	
		1.9	2.93	6.1		$V_{GS} = 2.5V, I_S = 6A$	
Diode Forward Voltage	V _{SS}	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 6A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	3039	_		10/1/	
Output Capacitance	Coss	_	530	_	pF	$V_{SS} = 10V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	141	_		1 - 11/11/2	
Total Gate Charge	Qg	_	35.7	_			
Gate-Source Charge	Q _{gs}	_	6.7	_	nC	$V_{SS} = 6V$, $V_{GS} = 4V$,	
Gate-Drain Charge	Q _{gd}	_	9.2	_	IIC	$I_S = 6A$	
Gate Charge at V _{TH}	Q _{g(th)}	_	3.4	_			
Turn-On Delay Time	t _{D(ON)}	_	880	_			
Turn-On Rise Time	t _R	_	1468	_		$V_{SS} = 6V, V_{GS} = 4V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	2914	_	ns	Is = 6A	
Turn-Off Fall Time	t _F	_	2830	_			

Notes:

- 5. Device mounted on FR-4 material with 1inch² (6.45cm²), 2oz. (0.071mm thick) Cu.
- 6. Repetitive rating, pulse width limited by junction temperature.
- 7. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to production testing.





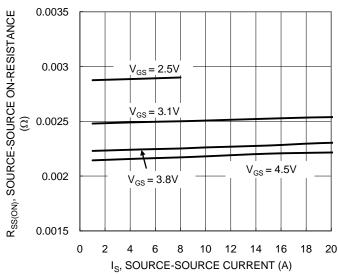


Figure 3. Typical On-Resistance vs. Source Current and Gate Voltage

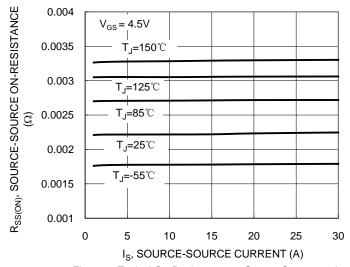


Figure 5. Typical On-Resistance vs. Source Current and Junction Temperature

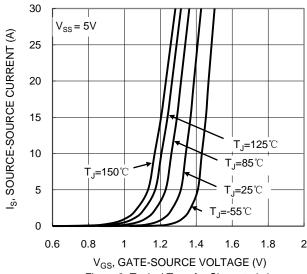
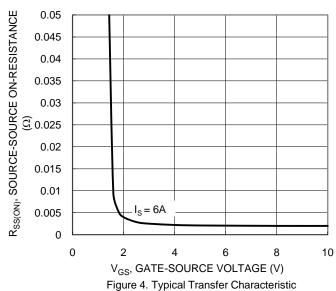


Figure 2. Typical Transfer Characteristic



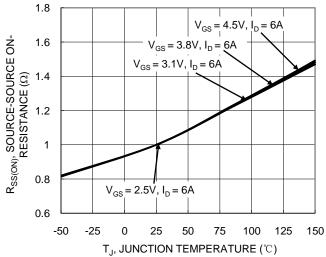
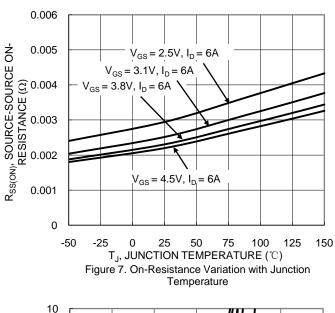
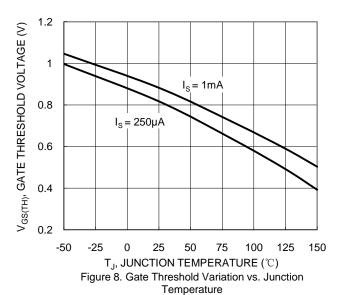


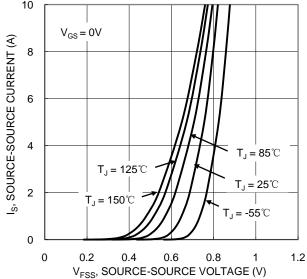
Figure 6. On-Resistance Variation with Junction Temperature

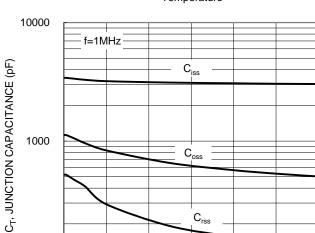












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V_{DS}, DRAIN-SOURCE VOLTAGE (V)

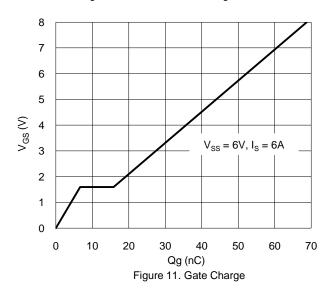
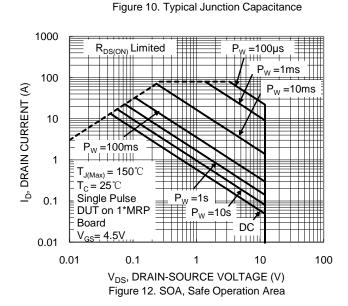


Figure 9. Diode Forward Voltage vs. Current



100

0

2

10

12



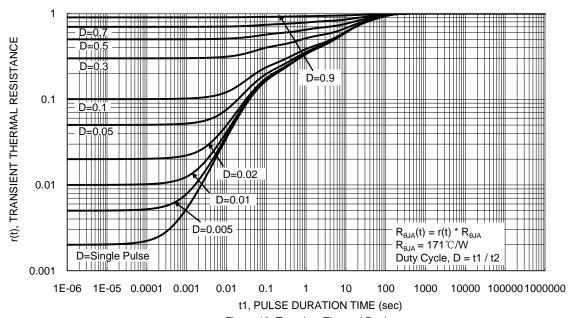
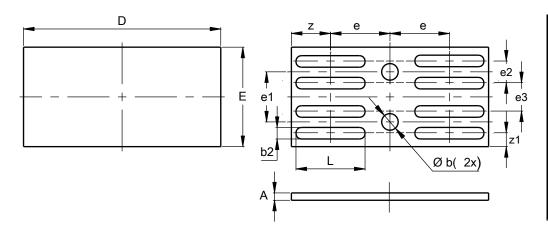


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X4-DSN3015-10



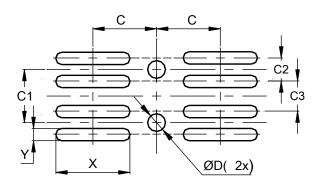
X4-DSN3015-10							
Dim	Min	Max	Тур				
Α	0.09	0.16	0.11				
b			0.25				
b2			0.175				
D	2.93	3.03	2.98				
Е	1.44	1.54	1.49				
е			0.895				
e1			0.75				
e2			0.325				
е3			0.425				
L			1.04				
Z			0.595				
z 1			0.2075				
All Dimensions in mm							



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X4-DSN3015-10



Dimensions	Value (in mm)
С	0.895
C1	0.750
C2	0.325
C3	0.425
D	0.25
Х	1.04
Y	0.175

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 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
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